





25V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -25V
- I_C = -3A high Continuous Current
- Low saturation voltage V_{CE(sat)} < -250mV @ -1A
- $R_{CE(sat)}$ = 93m Ω for a low equivalent On-Resistance
- hFE specified up to -6A for a high gain hold up
- Complementary NPN Type: FZT689B
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: SOT223
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (approximate)

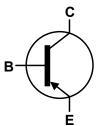
Applications

- Power MOSFET & IGBT gate driving
- Battery powered circuits
- Fast charge converters
- Low loss power switching

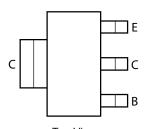
SOT223



Top View



Device Symbol



Top View Pin-Out

Ordering Information (Notes 4 & 5)

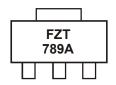
Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT789ATA	AEC-Q101	FZT789A	7	12	1,000
FZT789AQTA	Automotive	FZT789A	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.</p>
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com

Marking Information



FZT789A = Product Type Marking





FZT789A

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-30	V
Collector-Emitter Voltage	V _{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	I _{CM}	-6	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	D	2	W
Power Dissipation	(Note 7)	P_{D}	3	W
Thermal Resistance, Junction to Ambient	(Note 6)	ר	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	12.93	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C	

ESD Ratings (Note 9)

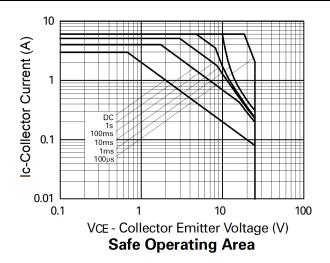
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

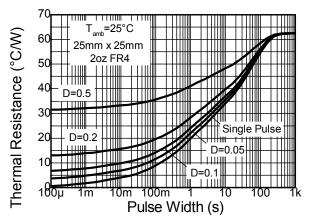
Notes:

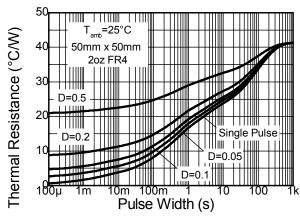
- 6. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; device measured when operating in steady state condition.
- 7. Same as note (6), except the device is mounted on 50mm X 50mm single sided 2oz weight copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information

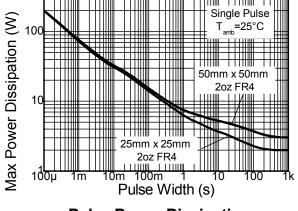


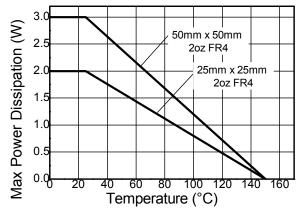




Transient Thermal Impedance

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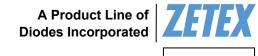




Pulse Power Dissipation

Derating Curve





FZT789A

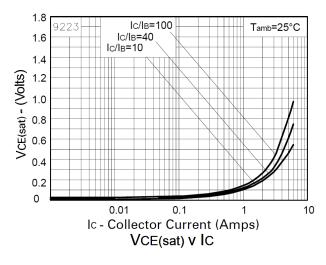
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

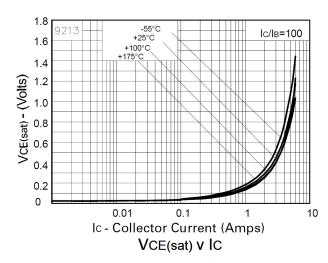
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-30	-40	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-25	-35	_	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.5	-	V	I _E = -100μA
Collector Cut-off Current	I _{CBO}	-	<1	-100	nA	V _{CB} = -15V
Collector Cut-on Current		_	_	-10	μΑ	V _{CB} = -15V, T _{amb} = 100°C
Collector Cut-off Current	I _{CES}	-	<1	-100	nA	V _{CE} = -15V
Emitter Cut-off Current	I _{EBO}	-	<1	-100	nA	V _{EB} = -5.6V
		-	-0.15	-0.25	V	$I_C = -1A$, $I_B = -10mA$
Collector-Emitter Saturation Voltage (Note 8)	V _{CE(sat)}	_	-0.30	-0.45		$I_C = -2A$, $I_B = -20mA$
			-0.30	-0.50		$I_C = -3A$, $I_B = -100mA$
Base-Emitter Saturation Voltage (Note 8)	V _{BE(sat)}	_	-0.80	-1.0	V	I _C = -1A, I _B = -10mA
Base-Emitter Turn-On Voltage (Note 8)	V _{BE(on)}	-	-0.75	-1.1	V	I _C = -1A, V _{CE} = -2V
	h _{FE}	300	-	800		$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 8)		250	-	-		$I_C = -1A$, $V_{CE} = -2V$
DC Current Gain (Note 8)		200	-	_	_	$I_C = -2A$, $V_{CE} = -2V$
		100	-	_		I _C = -6A, V _{CE} = -2V
Current Gain-Bandwidth Product (Note 8)	f _T	100	-	-	MHz	$V_{CE} = -5V, I_{C} = -50mA$ f = 50MHz
Turn-On Time	t _{on}	-	35	_	ns	$V_{CC} = -10V, I_{C} = -500mA$
Turn-Off Time	t _{off}	-	400	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$
Input Capacitance (Note 8)	C _{ibo}	-	225	_	pF	V _{EB} = -0.5V, f = 1MHz
Output Capacitance (Note 8)	C _{obo}		25		pF	V _{CB} = -10V, f = 1MHz

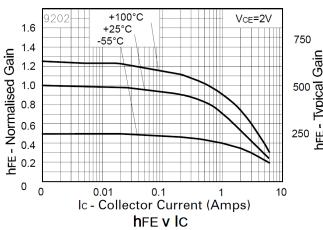
Notes: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

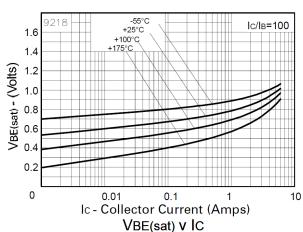


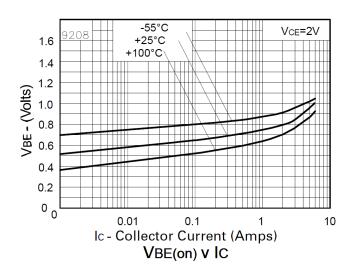
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







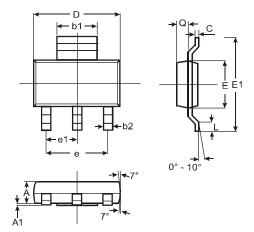






Package Outline Dimensions

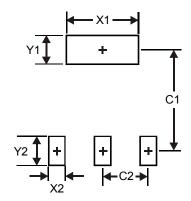
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1	_	_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3





FZT789A

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